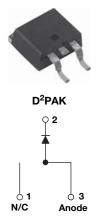
Vishay Semiconductors

RoHS

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



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PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK)					
I _{F(AV)}	4 A					
V _R	600 V					
V _F at I _F	1.8 V					
t _{rr} (typ.)	17 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- \bullet Very low Q_{rr}
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
 FREE
- AEC-Q101 qualified
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRRM) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Cathode to anode voltage	V _R		600	V				
Maximum continuous forward current	١ _F	T _C = 100 °C	4					
Single pulse forward current	I _{FSM}		25	А				
Maximum repetitive forward current	I _{FRM}		16					
Maximum neuror discinction	D	T _C = 25 °C 25		W				
Maximum power dissipation	PD	T _C = 100 °C	10	vv				
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C				

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1

Document Number: 94036

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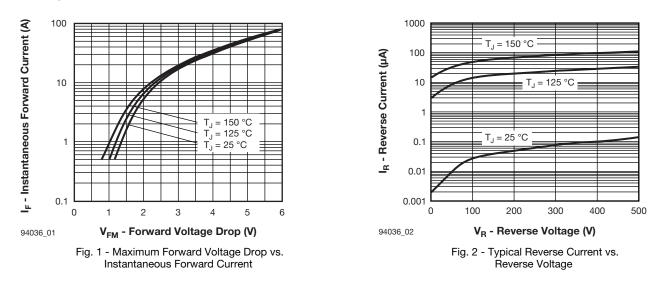
ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
		I _F = 4.0 A		-	1.5	1.8	v		
Maximum forward voltage	V_{FM}	I _F = 8.0 A	See fig. 1	-	1.8	2.2			
		I _F = 4.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse		V _R = V _R rated	Coofig 0	-	0.17	3.0			
leakage current	I _{RM}	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	44	300	μA		
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	4.0	8.0	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	ckage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5, 6	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}$	Vµs, V _R = 30 V	-	17	-	ns		
	t _{rr1}	T _J = 25 °C		-	28	42			
	t _{rr2}	T _J = 125 °C		-	38	57			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	2.9	5.2	A nC A/us		
	I _{RRM2}	T _J = 125 °C	I _F = 4.0 A	-	3.7	6.7			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	$dI_F/dt = 200 A/\mu s$	-	40	60			
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	70	105			
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	280	-			
	dl _{(rec)M} /dt2	T _J = 125 °C		-	235	-	Ανμs		

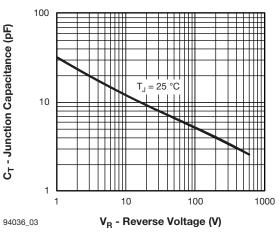
THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	r.∕ vv			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Marking device		Case style D ² PAK		HFA04	TB60S				

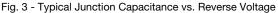
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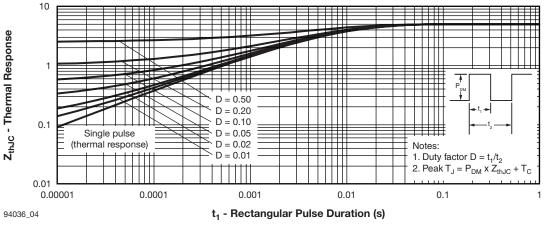
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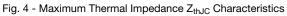


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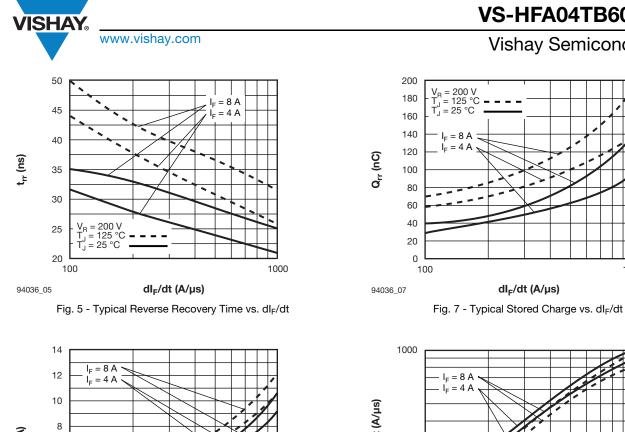






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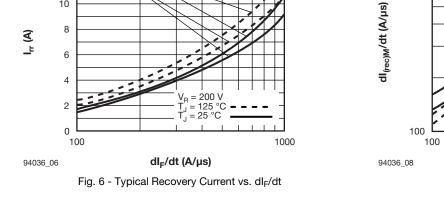
1000

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 $V_{R} = 200 V$ $T_{J} = 125 °C$ $T_{J} = 25 °C$

dl_F/dt (A/µs)

Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt





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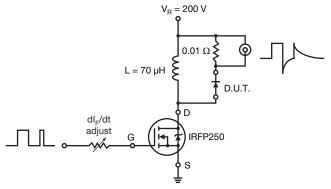


Fig. 9 - Reverse Recovery Parameter Test Circuit

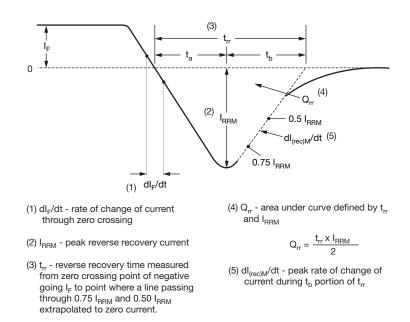


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	04	тв	60	S	TRL	PbF	
	1	2	3	4	5	6	7	8	9	
	 HPP product suffix HEXFRED[®] family 									
	 Process designator: A = Electron irradiated 									
	 4 - Current rating (04 = 4 A) 5 - Package outline (TB = TO-220, 2 leads) 									
	5 - 6 -		U	ng (60 =			eaus)			
	7 -		D ² PAK	0.	,					
	8 - • None = Tube (50 pieces)									
		 TRL = Tape and reel (left oriented) 								
	 TRR = Tape and reel (right oriented) 									
	9 -	• PbF	= Leac	l (Pb)-fre	ee					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95054					
Packaging information	www.vishay.com/doc?95032					



Outline Dimensions

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MIN.

0.270

0.380

0.311

0.575

0.070

0.050

0.188

0.100 BSC

0.010 BSC

MAX.

0.315

0.420

0.346

0.625

0.110

0.070

0.208

3

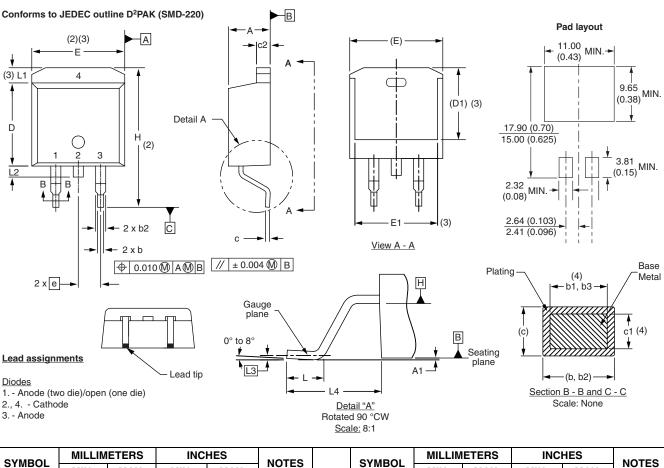
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З

3

D²PAK





SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	
С	0.38	0.74	0.015	0.029		L1	-	1.65	
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

 $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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